Phototransistor, surface mount type RPM-075PT

Quite new phototransistor which peak sensitivity is designed as same level as human eye. Best sensor to detect illuminance. (Peak sensitivity is 600nm.) Small and light weight package which can be used for reflow soldering and Pd free soldering.

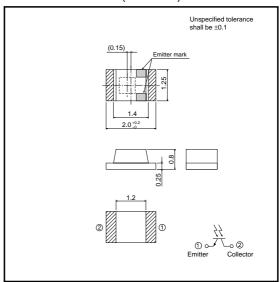
Application

Control of lighting cellular phones, LCD displays, etc. Control of strobe. (DSC, camcorder, etc.)

Features

- 1) Best sensor to detect illuminance. (Peak sensitivity is 600nm.)
- Small (2125) and light weight package (3mg) which can be used for reflow soldering and Pd free soldering.
- 3) Linear against wide range of illuminance from a few Lx to 10000Lx over.
- 4) Use Si good for an environ ment. (not CdS)

●External dimensions (Units : mm)



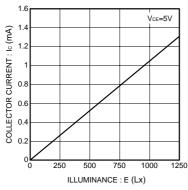
◆Absolute maximum ratings (Ta=25°C)

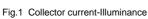
Parameter	Symbol Limits		Unit
Collector-emitter voltage	Vceo	20	V
Emitter-collector voltage	VECO	5	V
Collector current	Ic	10	mA
Collector power dissipation	Pc	50	mW
Operating temperature	Topr	-30~+85	°C
Storage temperature	Tstg	-40~+100	°C

●Electrical and optical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Light current	lc	0.25	0.4	0.6	mA	Vce=5V, E=500Lx
Dark current	ICEO	_	-	0.5	μΑ	VcE=10V (Black box)
Peak sensitivity wavelength	λР	_	600	-	nm	_
Collector-emitter saturation voltage	V _{CE(sat)}	-	-	0.4	٧	Ic=0.1mA, E=500Lx
Half-angle	θ1/2	-	±60	-	deg	_
Response time	tr∙tf	-	10	-	μs	Vcc=5V, Ic=1mA, RL=100Ω

Electrical and optical characteristic curves





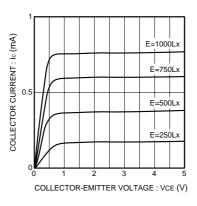


Fig.2 Output characteristics

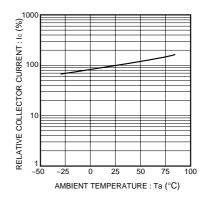


Fig.3 Relative output-Ambient temperature

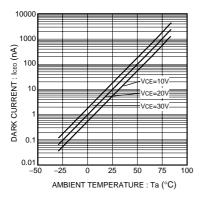


Fig.4 Dark current-Ambient temperature

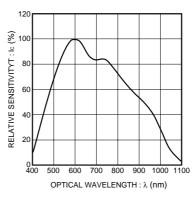


Fig.7 Spectral sensitivity characteristics

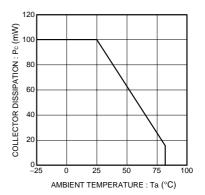


Fig.6 Collector dissipation -Ambient temperature

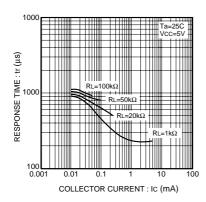


Fig.7 Response time-Collector current

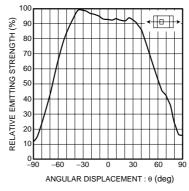


Fig.8 Directional pattern

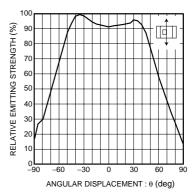


Fig.9 Directional pattern